

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

MMBD4148A/SE/CC/CA-MS

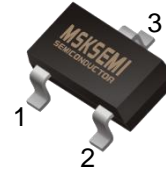
Product specification

FEATURE

- Fast Switching Speed z
- For General Purpose Switching Applications
- High Conductance

Reference News

SOT-23



Pin Configuration

MMBD4148A-MS	MMBD4148CA-MS	MMBD4148CC-MS	MMBD4148SE-MS

MARKING

MMBD4148A-MS	MMBD4148CA-MS	MMBD4148CC-MS	MMBD4148SE-MS
5H	D6	D5	D4

Maximum Ratings @Ta=25°C

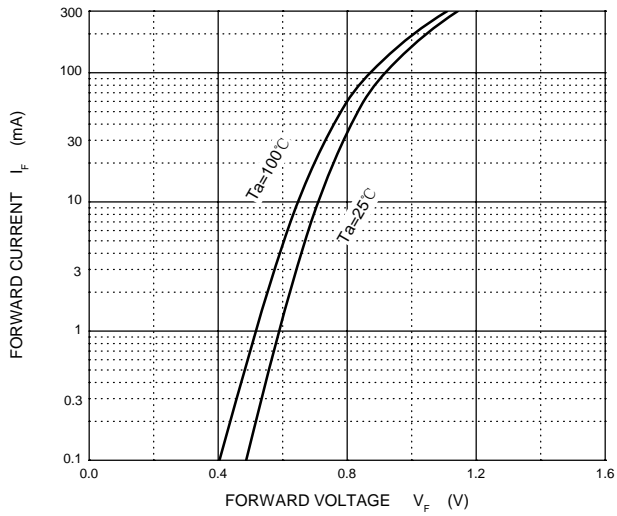
Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Peak Reverse Voltage	V_{RRM}		
Working Peak Reverse Voltage	V_{RWM}	100	V
DC Blocking Voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Output Current	I_o	200	mA
Peak Forward Surge Current @t=1.0μs @ t=1.0s	I_{FSM}	2.0 1.0	A
Power Dissipation	P_D	350	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	357	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

Electrical Ratings @Ta=25°C

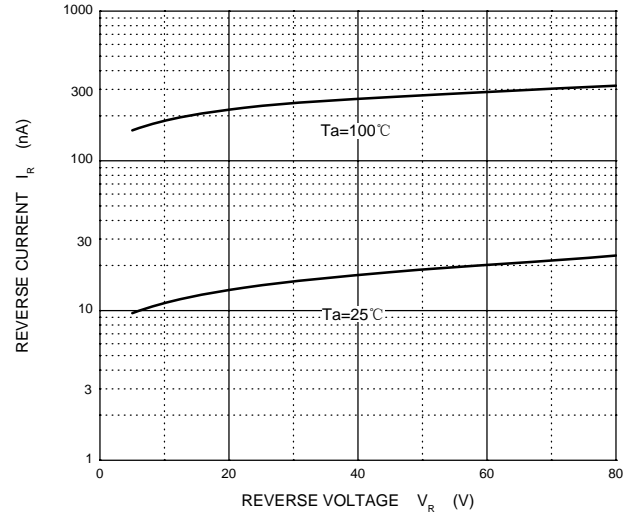
Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	$V_{(BR)1}$	100			V	$I_R=100\mu A$
	$V_{(BR)2}$	75			V	$I_R=5\mu A$
Forward voltage	V_F			1	V	$I_F=10mA$
Reverse current	I_{R1}			5	μA	$V_R=75V$
	I_{R2}			25	nA	$V_R=25V$
Capacitance between terminals	C_T			4	pF	$V_R=0V, f=1MHz$
Reverse recovery time	t_{rr}			4	ns	$I_F=I_R=10mA, V_R=6V,$ $I_{rr}=0.1 \times I_R, R_L=100\Omega$

Typical Characteristics

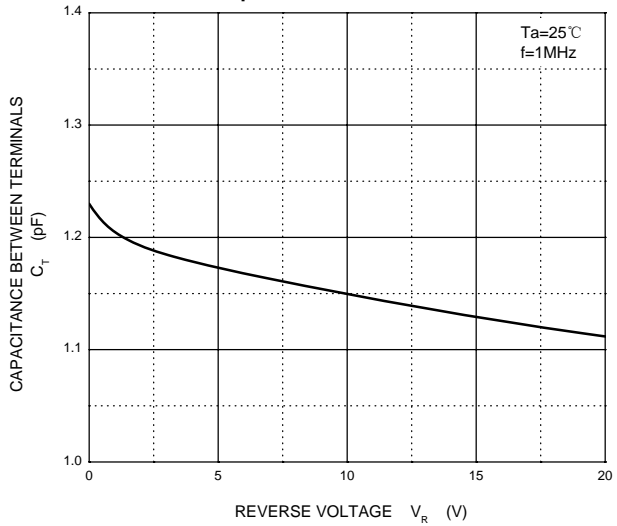
Forward Characteristics



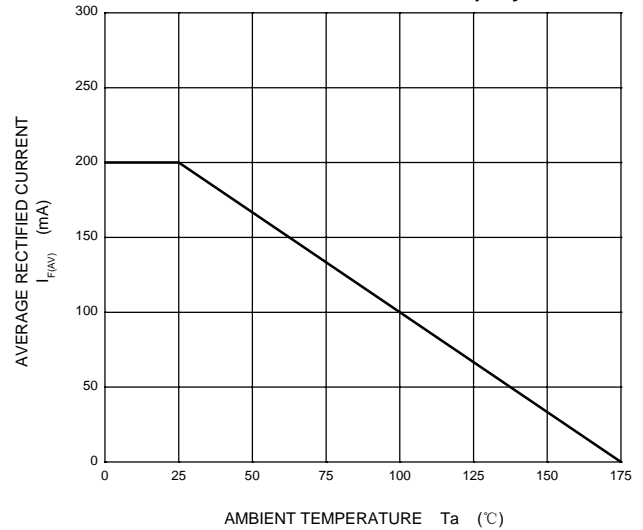
Reverse Characteristics



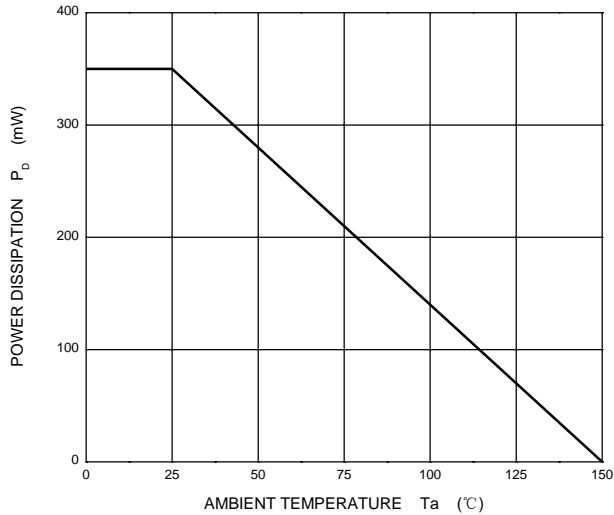
Capacitance Characteristics



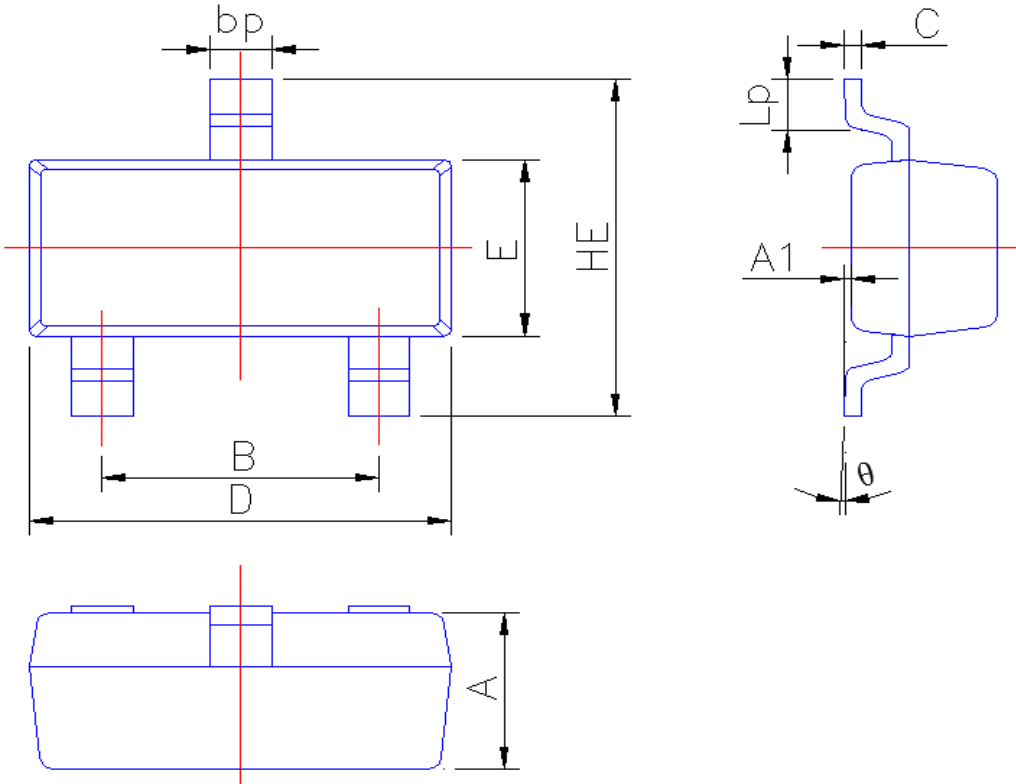
Semiconductor Intrinsic Property



Power Derating Curve



PACKAGE MECHANICAL DATA



SOT-23

Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.10
A1	0.013	0.100
B	1.80	2.00
bp	0.35	0.50
C	0.09	0.150
D	2.80	3.00
E	1.20	1.40
HE	2.20	2.80
Lp	0.20	0.50
θ	0°	5°

REEL SPECIFICATION

P/N	PKG	QTY
MMBD4148A/SE/CC/CA-MS	SOT-23	3000

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